

Notice of References Cited	Application/Control No. 10/551,843		Applicant(s)/Patent Under Reexamination OHMI ET AL.	
	Examiner Grant S. Withers		Art Unit 2812	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2006/0194451	08-2006	Lee et al.	438/786
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	WO01/66832	03-2001	PCT	Werkhoven et al.	
	O	WO2005/015621	07-2003	PCT	Lim et al.	
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Koyama, Masato "Effects of Nitrogen in HfSiON Gate Dielectric on the Electrical and Thermal Characteristics" 2002 IEEE IEDM pp 849-852
	V	International Preliminary Examination Report for PCT/EP 03/50352
	W	Gordon, Roy "Vapor Deposition of Metal Oxides and Silicates: Possible Gate Insulators for Future Microelectronics" Chem. Mater. 2001 13 pp 2463-2464
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.